

**Features:**

- Isolated mounting base 3000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

V_{RRM}, V_{DRM}	Type & Outline		
2000V	MTx1000-20-411F3	MFx1000-20-411F3	
2200V	MTx1000-22-411F3	MFx1000-22-411F3	
2500V	MTx1000-25-411F3	MFx1000-25-411F3	
2500V	MT1000-25-411F3G		

MTx stands for any type of **MTC**, **MTA**, **MTK**MFx stands for any type of **MFC**, **MFA**, **MFK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_{HS}=55^\circ\text{C}$	125			1000	A
$I_{T(RMS)}$	RMS on-state current					1570	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			50	mA
I_{TSM}	Surge on-state current			125		18.0	kA
I^2t	I^2t for fusing coordination	$V_R=60\%V_{RRM}$, $t=10\text{ms}$ half sine	125			1620	$10^3\text{A}^2\text{s}$
V_{TO}	Threshold voltage			125		0.85	V
r_T	On-state slope resistance					0.24	$\text{m}\Omega$
V_{TM}	Peak on-state voltage			25		2.20	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			1000	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	125			200	$\text{A}/\mu\text{s}$
I_{GT}	Gate trigger current	$V_A=12\text{V}$, $I_A=1\text{A}$	25	30		200	mA
V_{GT}	Gate trigger voltage			0.8		3.0	V
I_H	Holding current			10		200	mA
I_L	Latching current					1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.20	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.048	$^\circ\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.024	$^\circ\text{C}/\text{W}$
V_{iso}	Isolation voltage	50Hz, R.M.S, $t=1\text{min}$, $I_{iso}=1\text{mA}(\text{MAX})$		3000			V
F_m	Terminal connection torque(M12)			12		16	$\text{N}\cdot\text{m}$
	Mounting torque(M8)			10		12	$\text{N}\cdot\text{m}$
T_{vj}	Junction temperature			-40		125	°C
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				3230		g
Outline		411F3					

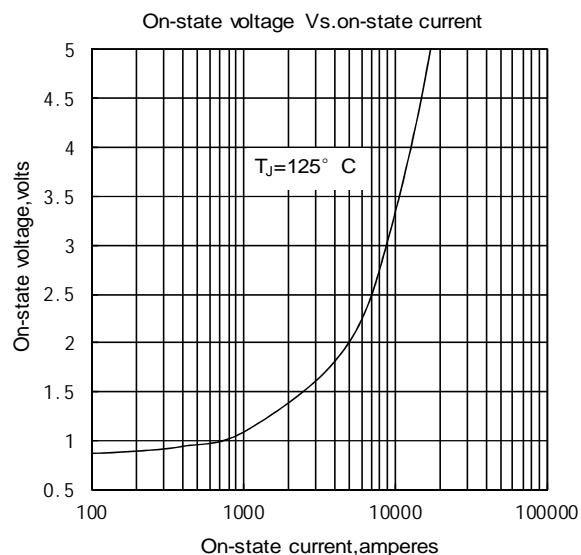


Fig.1

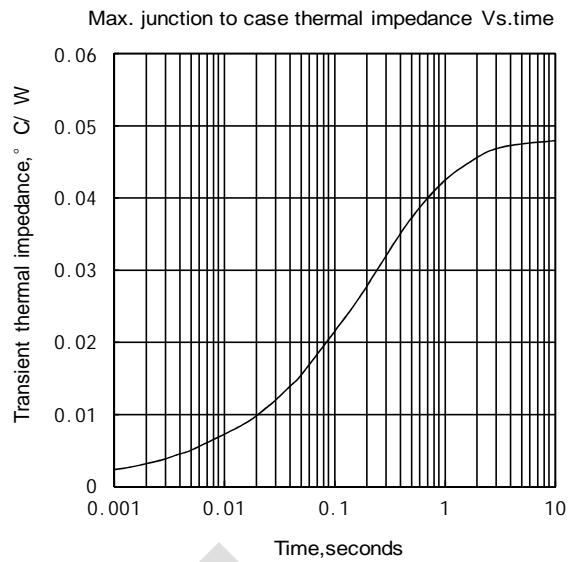


Fig.2

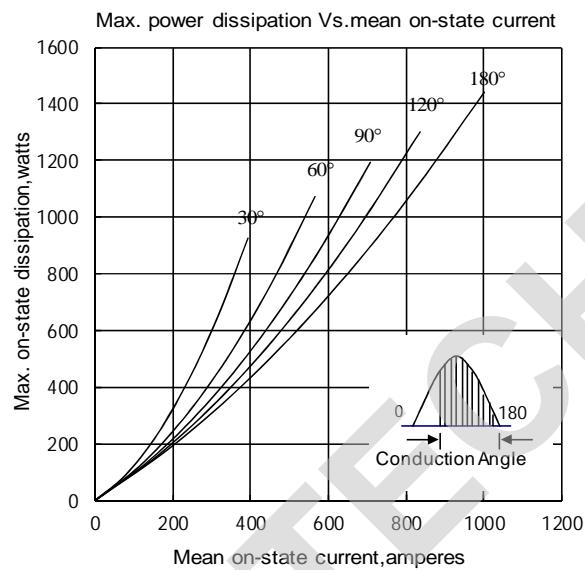


Fig.3

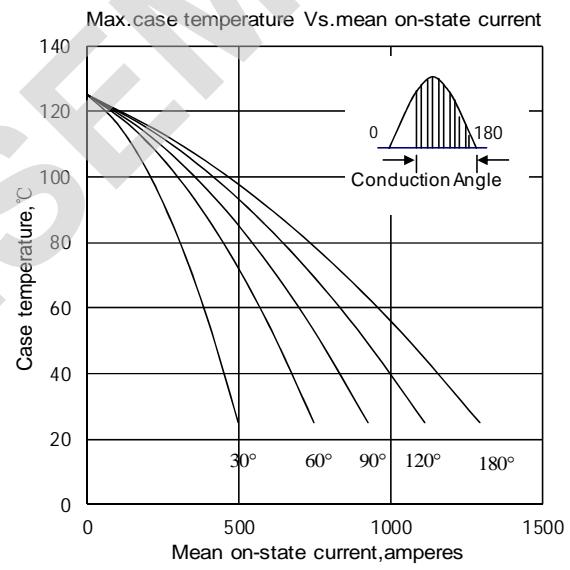


Fig.4

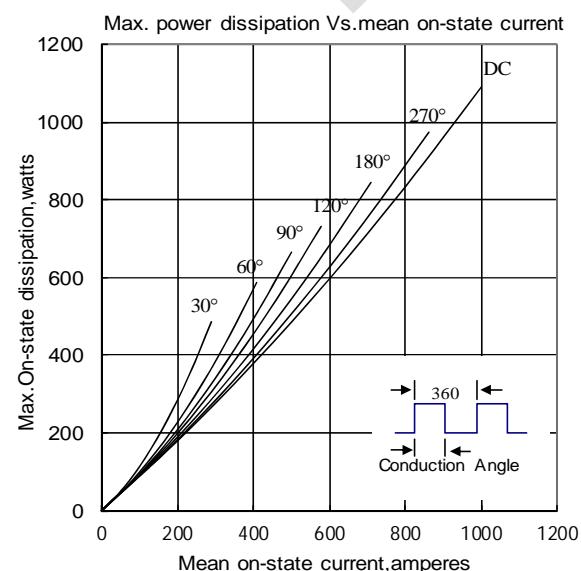


Fig.5

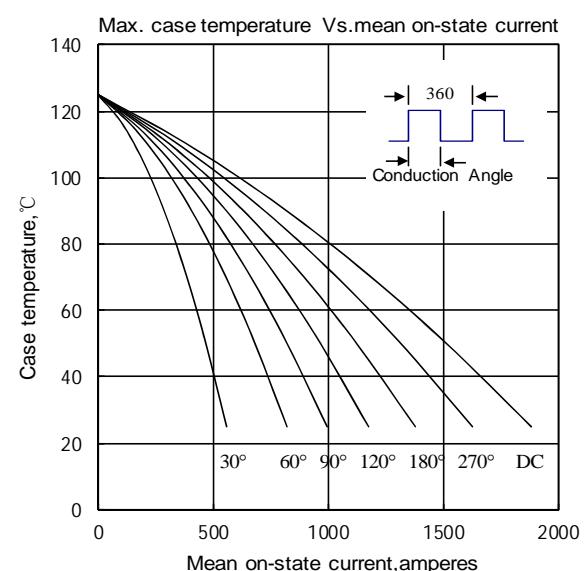


Fig.6

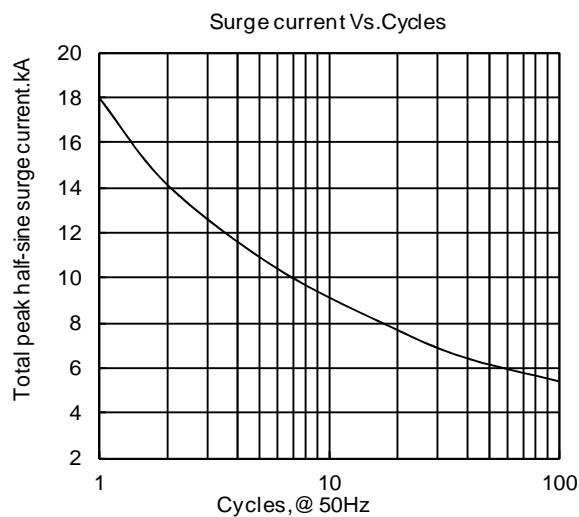


Fig. 7

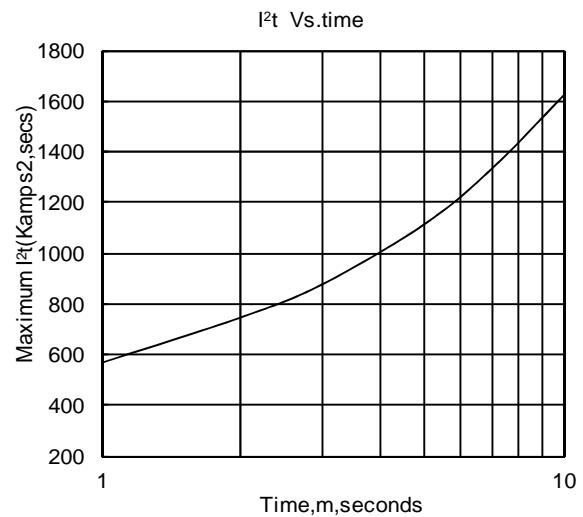


Fig. 8

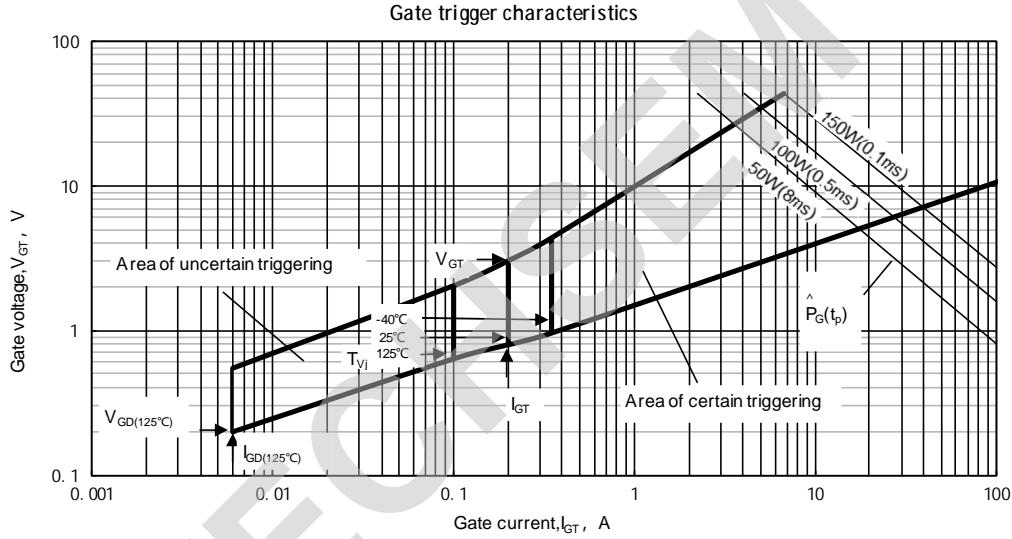
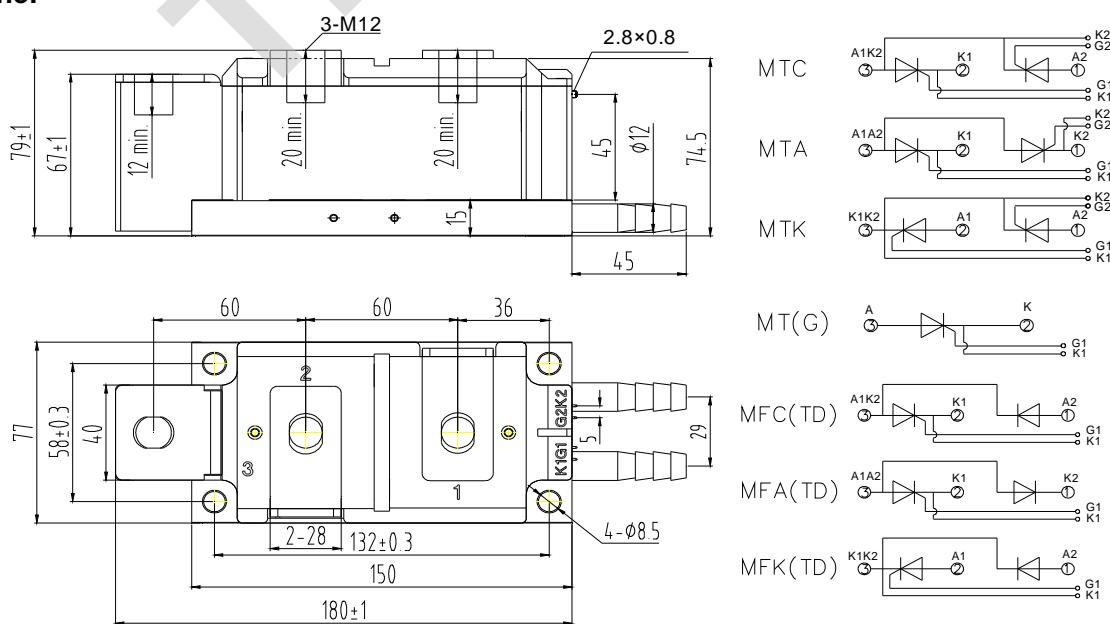


Fig. 9

Outline:**Unmarked dimensional tolerance: $\pm 0.5\text{mm}$**

TECHSEM reserves the right to change specifications without notice.